

ABSTRACT

The present invention discloses a transfer method of thin wafer. For thin wafers with different thicknesses, in different transfer stages, a Bernoulli manipulator uses different gas flow rates, so that the problem of chipping of wafers during transfer is solved. Specifically, in a process of moving a wafer out of a wafer cassette, a Bernoulli manipulator uses a small gas flow rate, so as to reduce the suction force on the wafer and weaken warping deformation of the wafer, thereby reducing the risk of cracking or chipping in the process of moving the wafer out of the wafer cassette; after the wafer is moved out of the wafer cassette and in a process of transferring same to a processing chamber, the Bernoulli manipulator uses a large gas flow rate, so as to increase the suction force on the wafer, thereby ensuring the wafer can be stably suctioned on the Bernoulli manipulator during transfer, and avoiding wafer slipping.